

KEY FEATURES

- MOCVD Epitaxy.
- 2/3/4/6 Inch.
- Excellent Beam Quality.
- High Power & Efficiency.
- High Uniformity & Reliability.

APPLICATIONS

- Materials Processing.
- Laser Pumps.
- Medical / Aesthetics

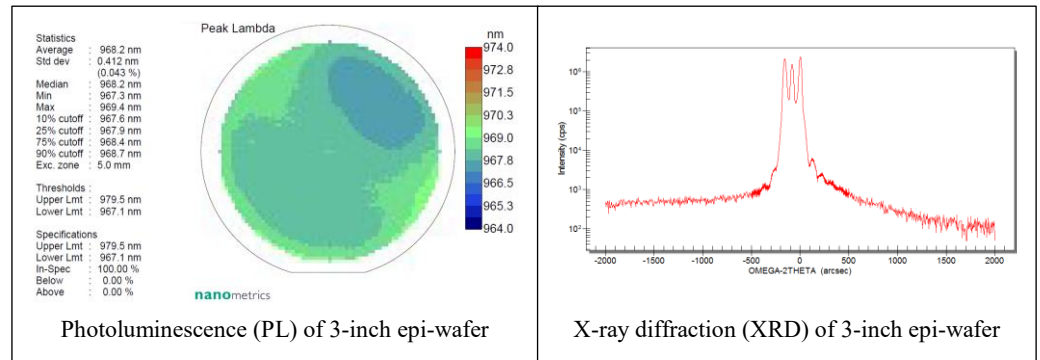
● PRODUCT DESCRIPTION

The 980 nm Fabry-Perot (FP) laser diode (LD) epi-wafer, designed especially for the high-power characteristics, is grown by metal-organic chemical vapor deposition (MOCVD) by Huaxing OPTO, with with strained InGaAs quantum well as the active layer.

● EPITAXY STRUCTURE

p+-GaAs Contact
p-AlGaAs Cladding
Waveguide
Active layer
Waveguide
n-AlGaAs Cladding
n-GaAs Buffer
n-GaAs Substrate

● WAFER CHARACTERIZATION



● TYPICAL EPITAXY PARAMETERS

Parameters	Values
Thickness control	<±5%
Thickness uniformity	<±3%
PL wavelength uniformity	<±3 nm
Doping control	<±30%
Mole Fraction (x) Tolerance	<±2%

● TYPICAL DEVICE PERFORMANCE

Parameters	Typical Values
Threshold current@25°C	65mA
Wavelength	980 nm
Slope efficiency	0.55 W/A
Ridge waveguide	30 μm×1000 μm, as cleaved facet @ RT



FOCUSING ON EPITAXIAL WAFER

PRECISE, EFFICIENT AND PROFESSIONAL